# Abstracts

## Extraction Techniques for FET Switch Modeling

*A. Ehoud, L.P. Dunleavy, S.C. Lazar and R.E. Branson. "Extraction Techniques for FET Switch Modeling." 1995 Transactions on Microwave Theory and Techniques 43.8 (Aug. 1995 [T-MTT]): 1863-1868.*

A new simple method for extracting equivalent circuit parameters for series and shunt GaAs FET switches is presented. The circuit elements are extracted from one set of S-parameter measurements for each switch state, and scale linearly with gate width. Extracted Equivalent Circuit Parameters (ECP's) are insensitive to frequency across the measured bandwidth. Good agreement has been obtained between simulated and model results for a 0.5 µm gate length series and shunt GaAs FET switches of varying gate widths, across the 0.45-26.5 GHz band.

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